

SOT23 PNP SILICON PLANAR MEDIUM POWER TRANSISTORS

FMMT549
FMMT549A

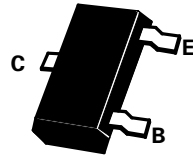
ISSUE 3 - OCTOBER 1995

FEATURES

- * Low equivalent on-resistance; $R_{CE(sat)} 250m\Omega$ at 1A
- * 1 Amp continuous current

COMPLEMENTARY TYPES – FMMT549 – FMMT449
FMMT549A – N/A

PARTMARKING DETAIL – FMMT549 – 549
FMMT549A – 59A



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-35	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-2	A
Continuous Collector Current	I_C	-1	A
Base Current	I_B	-200	mA
Power Dissipation: at $T_{amb}=25^{\circ}C$	P_{tot}	500	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Breakdown Voltages	$V_{(BR)CBO}$	-35			V	$I_C=-100\mu A$
	$V_{(BR)CEO}$	-30			V	$I_C=-10mA^*$
	$V_{(BR)EBO}$	-5			V	$I_E=-100\mu A$
Cut-Off Currents	I_{CBO}			-0.1 -10	μA μA	$V_{CB}=-30V$ $V_{CB}=-30V, T_{amb}=100^{\circ}C$
	I_{EBO}			-0.1	μA	$V_{EB}=-4V$
	$I_{CE(sat)}$		-0.25 -0.50	-0.50 -0.75	V V	$I_C=-1A, I_B=-100mA^*$ $I_C=-2A, I_B=-200mA^*$
Saturation Voltages	$V_{BE(sat)}$			-0.30	V	$I_C=-100mA, I_B=-1mA^*$
			-0.9	-1.25	V	$I_C=-1A, I_B=-100mA^*$
Base Emitter Turn-on Voltage	$V_{BE(on)}$		-0.85	-1	V	$I_C=-1A, V_{CE}=-2V^*$
Static Forward Current Transfer Ratio	h_{FE}	70 80 40	200 130 80			$I_C=-50mA, V_{CE}=-2V^*$ $I_C=-1A, V_{CE}=-2V^*$ $I_C=-2A, V_{CE}=-2V^*$
	FMMT549	100	160	300		$I_C=-500mA, V_{CE}=-2V^*$
	FMMT549A	150	200	500		$I_C=-500mA, V_{CE}=-2V^*$
Transition Frequency	f_T	100			MHz	$I_C=-100mA, V_{CE}=-5V$ $f=100MHz$
Output Capacitance	C_{obo}			25	pF	$V_{CB}=-10V, f=1MHz$
Switching Times	t_{on}		50		ns	$I_C=-500mA, V_{CC}=-10V$
	t_{off}		300		ns	$I_{B1}=I_{B2}=-50mA$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

FMMT549 **FMMT549A**

TYPICAL CHARACTERISTICS

